

# NPN General Purpose Transistor

BC848BW / BC848B / BC848C

●Features

- 1)  $V_{CE0}$  minimum is 30V ( $I_C=1mA$ )
- 2) Complements the BC858B / BC858BW.

●Package, marking and packaging specifications

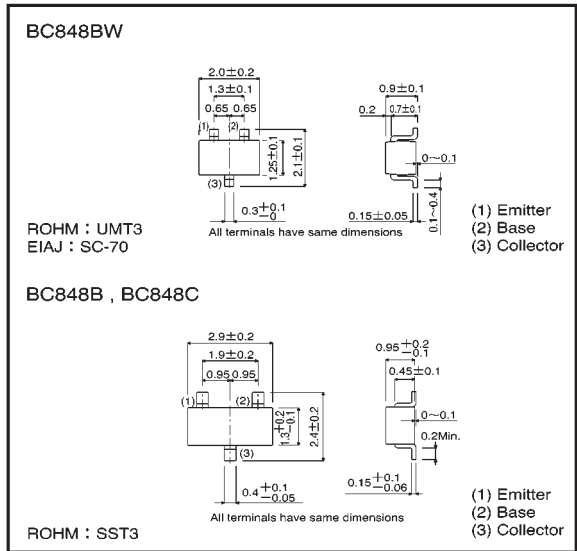
Part No.	BC848BW	BC848B	BC848C
Packaging type	UMT3	SST3	SST3
Marking	G1K	G1K	G1L
Code	T106	T116	T116
Basic ordering unit (pieces)	3000	3000	3000

●Absolute maximum ratings ( $T_a=25^{\circ}C$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	30	V
Collector-emitter voltage	$V_{CEO}$	30	V
Emitter-base voltage	$V_{EB0}$	5	V
Collector current	$I_C$	0.1	A
Collector power dissipation	$P_C$	0.2	W
		0.35	
Junction temperature	$T_J$	150	$^{\circ}C$
Storage temperature	$T_{stg}$	$-55 \sim +150$	$^{\circ}C$

\* When mounted on a 7 x 5 x 0.6 mm ceramic board.

●External dimensions (Units : mm)



●Electrical characteristics ( $T_a=25^{\circ}C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	30	—	—	V	$I_C=50 \mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	30	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	$BV_{EB0}$	5	—	—	V	$I_E=50 \mu A$
Collector cutoff current	$I_{CBO}$	—	—	15	$\mu A$	$V_{CB}=30V$
		—	—	5		$V_{CB}=30V, T_a=150^{\circ}C$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.25	V	$I_C/I_E=10mA/0.5mA$
		—	—	0.6		$I_C/I_E=100mA/5mA$
Base-emitter saturation voltage	$V_{BE(on)}$	0.58	—	0.77	V	$V_{CE}/I_C=5V/10mA$
DC current transfer ratio	$h_{FE}$	200	—	450	—	$V_{CE}/I_C=5V/2mA$ (BC848B/BW)
		420	—	800		$V_{CE}/I_C=5V/2mA$ (BC848C)
Transition frequency	$f_T$	—	200	—	MHz	$V_{CE}=5V, I_E=-20mA, f=100MHz$
Collector output capacitance	$C_{ob}$	—	3	—	pF	$V_{CB}=10V, I_E=0, f=1MHz$
Collector output capacitance	$C_{ib}$	—	8	—	pF	$V_{EB}=0.5V, I_E=0, f=1MHz$

(SPEC-C22)

●Electrical characteristic curves

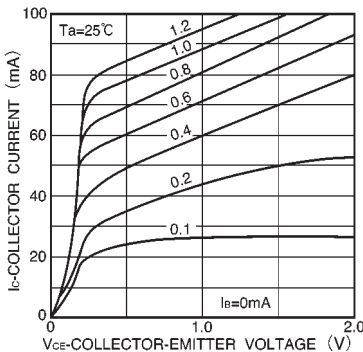


Fig.1 Grounded emitter output characteristics (I)

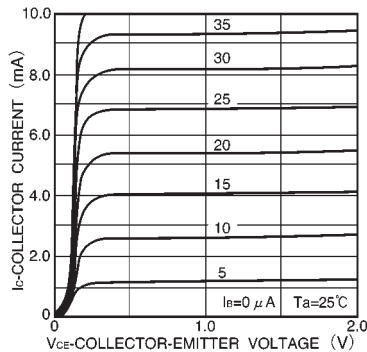


Fig.2 Grounded emitter output characteristics (II)

(SPEC-C22)

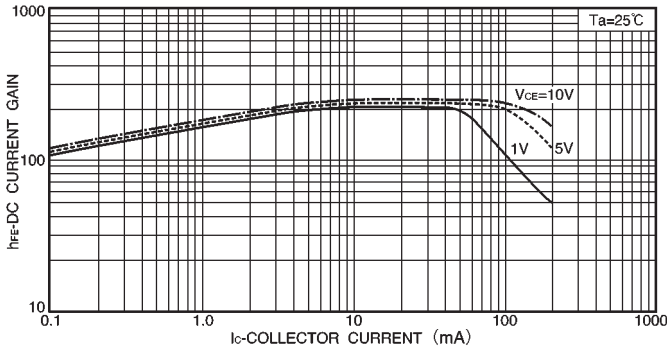


Fig.3 DC current gain vs. collector current ( I )

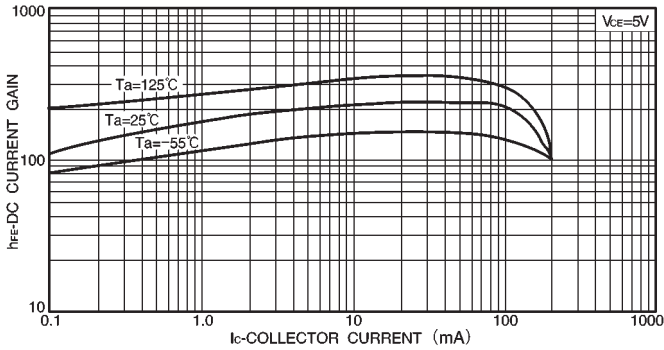


Fig.4 DC current gain vs. collector current ( II )

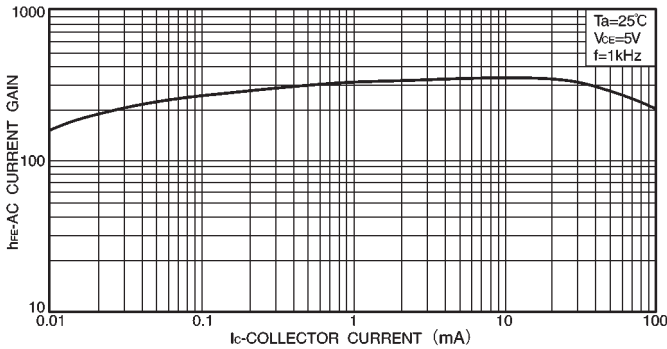


Fig.5 AC current gain vs. collector current

●Electrical characteristic curves

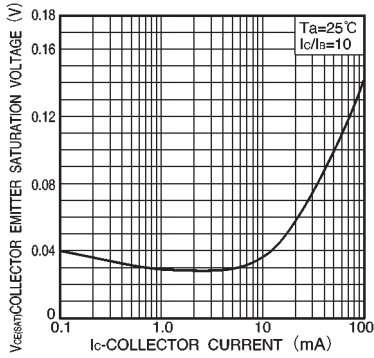


Fig.6 Collector-emitter saturation voltage vs. collector current

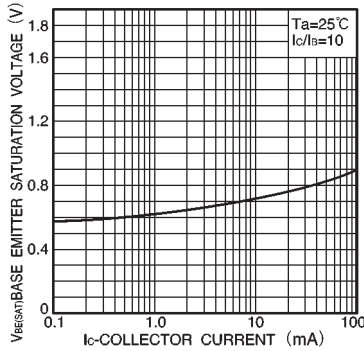


Fig.7 Base-emitter saturation voltage vs. collector current

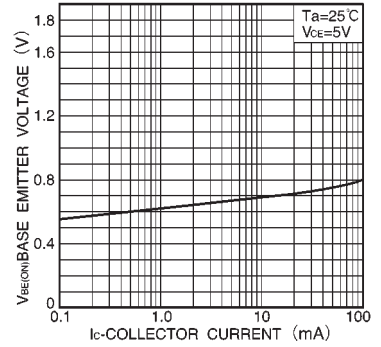


Fig.8 Grounded emitter propagation characteristics

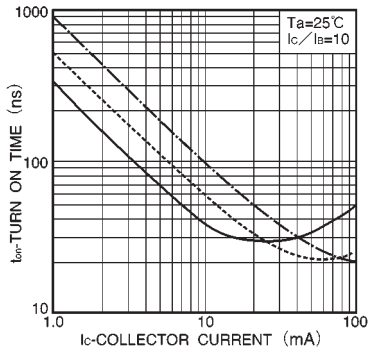


Fig.9 Turn-on time vs. collector current

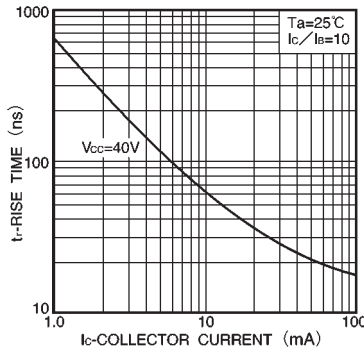


Fig.10 Rise time vs. collector current

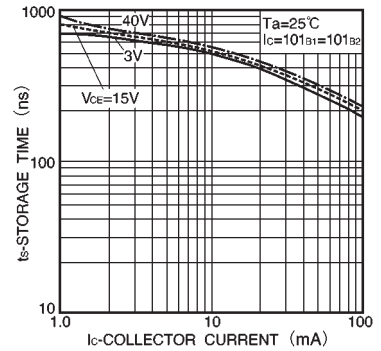


Fig.11 Storage time vs. collector current

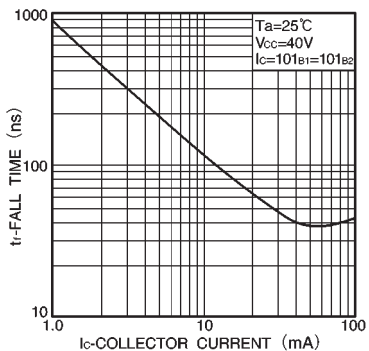


Fig.12 Fall time vs. collector current

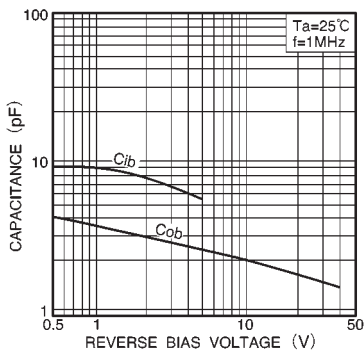


Fig.13 Input/output capacitance vs. voltage

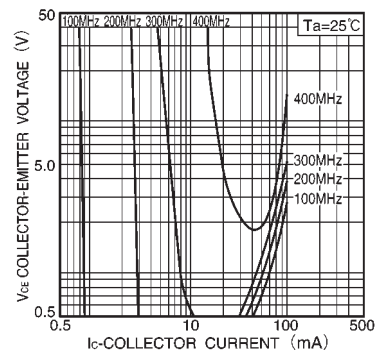


Fig.14 Gain bandwidth product

●Electrical characteristic curves

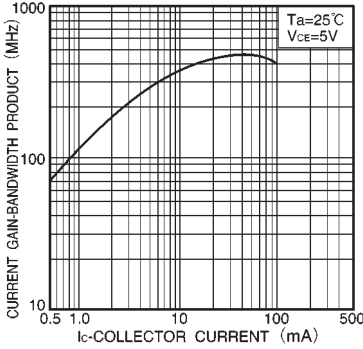


Fig.15 Gain bandwidth product vs. collector current

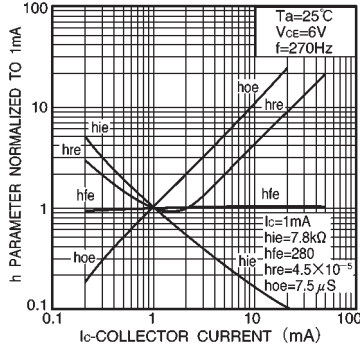


Fig.16 h parameter vs. collector current

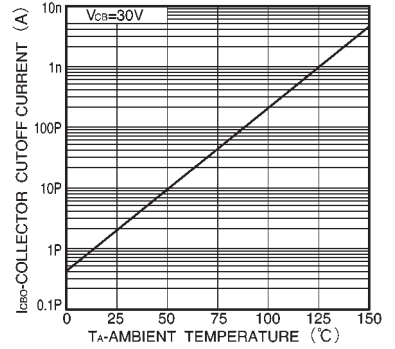


Fig.17 Collector cutoff current

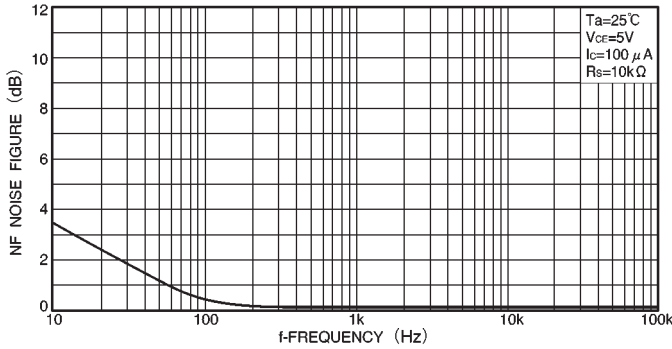


Fig.18 Noise vs. collector current

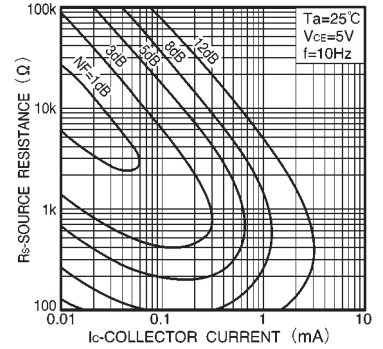


Fig.19 Noise characteristics (I)

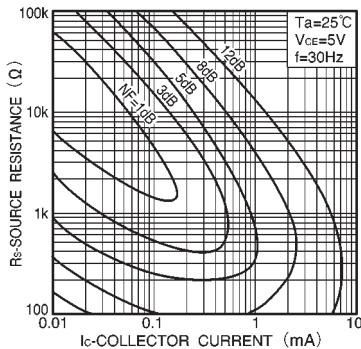


Fig.20 Noise characteristics (II)

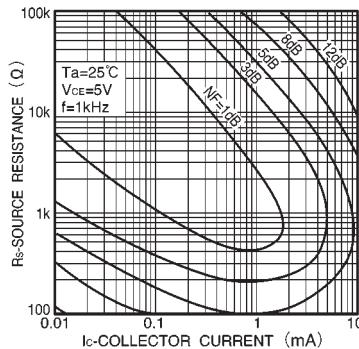


Fig.21 Noise characteristics (III)

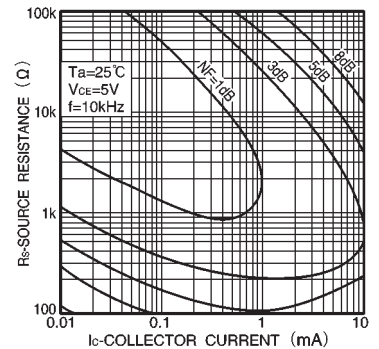


Fig.22 Noise characteristics (IV)